TDSEMIC
拓電半導體

自主封測 品質把控 售後保障

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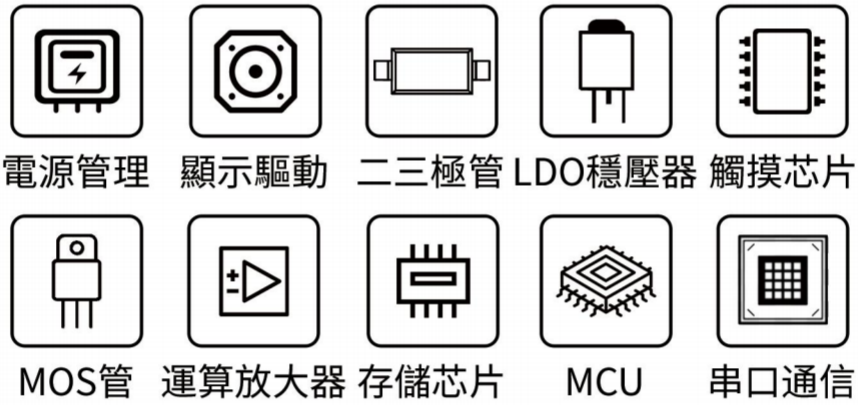


TD100N06

產品規格說明書

TDSEMIC

N沟道增强型场效应晶体管
N-CHANNEL MOSFET
TD100N06

Features

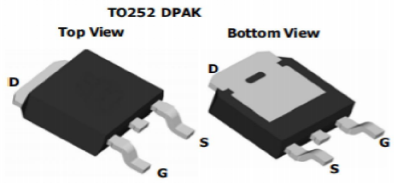
- Excellent $R_{DS(ON)}$ and Low Gate Charge
- 100% UIS Tested
- 100% ΔVds Tested
- Halogen-free; RoHS-compliant

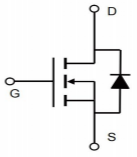
Applications

- Load Switch
- PWM Application
- Power Management

Product Summary

Parameters	Value	Unit
V_{DSS}	60	V
$V_{GS(th)_Typ}$	3.0	V
I_D(@V_{GS}=10V)	90	A
$R_{DS(ON)_Typ}$(@V_{GS}=10V	5.4	mΩ





Schematic

Ordering Information

Device	Marking	MSL	Form	Package	Reel(pcs)	Per Carton (pcs)
TD100N06	TD100N06	3	Tape&Reel	TO-252	2500	25000

Absolute Maximum Ratings (@ T_C = 25°C unless otherwise specified)

Symbol	Parameter		Value	Unit
V_{DS}	Drain-to-Source Voltage		60	V
V_{GS}	Gate-to-Source Voltage		±20	V
I_D	Continuous Drain Current	T_C = 25°C	90	A
		T_C = 100°C	51	
I_{DM}	Pulsed Drain Current (1)		Refer to Fig.4	A
E_{AS}	Single Pulsed Avalanche Energy (2)		168	mJ
P_D	Power Dissipation	T_C = 25°C	40	W
		T_C = 100°C	16	
T_J, T_{STG}	Junction & Storage Temperature Range		-55 to 150	°C

Thermal Characteristics

Symbol	Parameter	Max	Unit
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient(3)	38	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction to Case	3.1	

Electrical Characteristics (T_J = 25°C unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	I_D = 250 μA, V_{GS} = 0V	60	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 60V, V_{GS} = 0V	-	-	1.0	μA
I_{GSS}	Gate-Body Leakage Current	V_{DS} = 0V, V_{GS} = ±20V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250 μA	2.1	3.0	4.0	V
$R_{DS(ON)}$	Static Drain-Source ON-Resistance(4)	V_{GS} = 10V, I_D = 30A	-	5.4	6.6	mΩ
Dynamic Characteristics						
R_g	Gate Resistance	f = 1MHz	-	0.8	-	Ω
C_{iss}	Input Capacitance	V_{GS} = 0V, V_{DS} = 30V, f = 1MHz	2645	3703	4999	pF
C_{oss}	Output Capacitance		190	266	359	pF
C_{rss}	Reverse Transfer Capacitance		165	232	313	pF
Q_g	Total Gate Charge	V_{GS} = 0 to 10V V_{DS} = 30V, I_D = 30A	57	80	108	nC
Q_{gs}	Gate Source Charge		16	22	30	nC
Q_{gd}	Gate Drain("Miller") Charge		20	28	38	nC
Switching Characteristics						
$t_{d(on)}$	Turn-On DelayTime	V_{GS} = 10V, V_{DD} = 30V I_D= 30A, R_{GEN} = 3Ω	-	44	-	ns
t_r	Turn-On Rise Time		-	65	-	ns
$t_{d(off)}$	Turn-Off DelayTime		-	128	-	ns
t_f	Turn-Off Fall Time		-	77	-	ns
Body Diode Characteristics						
I_S	Maximum Continuous Body Diode Forward Current		-	-	90	A
I_{SM}	Maximum Pulsed Body Diode Forward Current		-	-	320	A
V_{SD}	Body Diode Forward Voltage	V_{GS} = 0V, I_S = 30A	-		1.2	V
trr	Body Diode Reverse Recovery Time	I_F = 30A, di/dt = 100A/us	72	101	136	ns
Qrr	Body Diode Reverse Recovery Charge		-	324	-	nC

Notes:

1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
2. E_{AS} condition: Starting T_J=25C, V_{DD}=30V, V_{GS}=10V, R_G=25ohm, L=0.5mH, I_{AS}=25.9A, V_{DD}=0V during time in avalanche.
3. $R_{\theta JA}$ is measured with the device mounted on a 1inch² pad of 2oz copper FR4 PCB.
4. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%.

Typical Performance Characteristics

Figure 1: Power De-rating

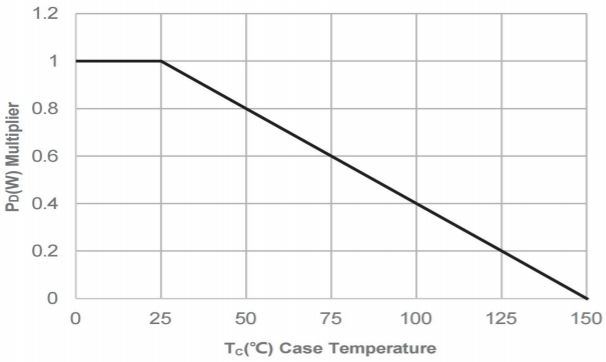


Figure 2: Current De-rating

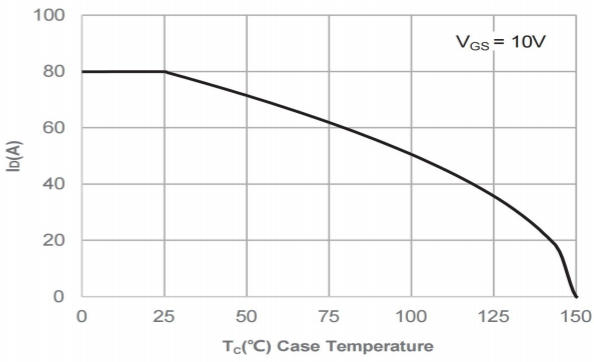


Figure 3: Normalized Maximum Transient Thermal Impedance

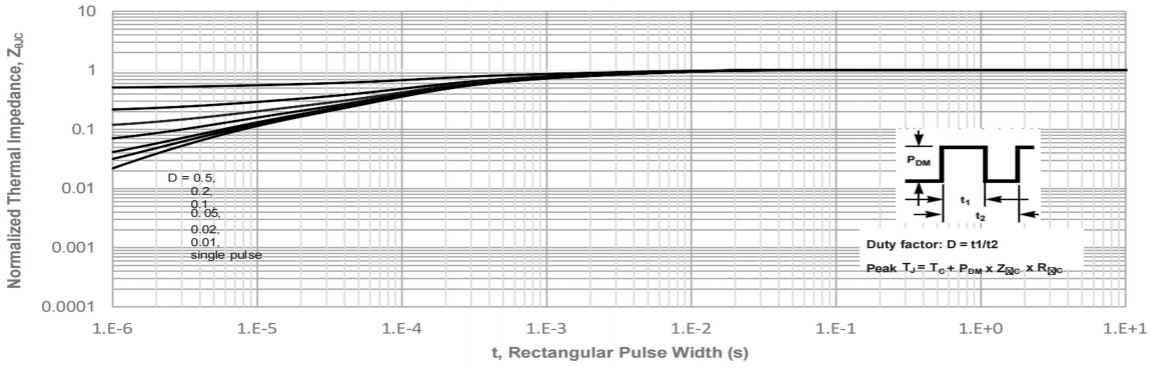
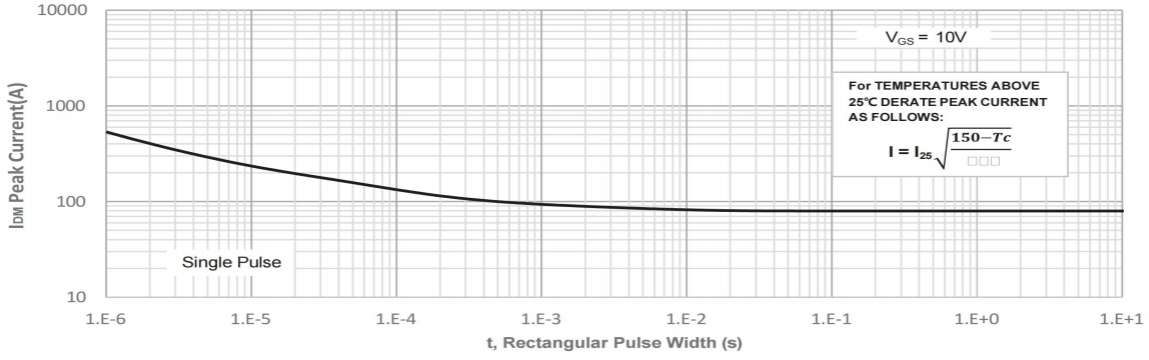


Figure 4: Peak Current Capacity



Typical Performance Characteristics

Figure 5: Output Characteristics

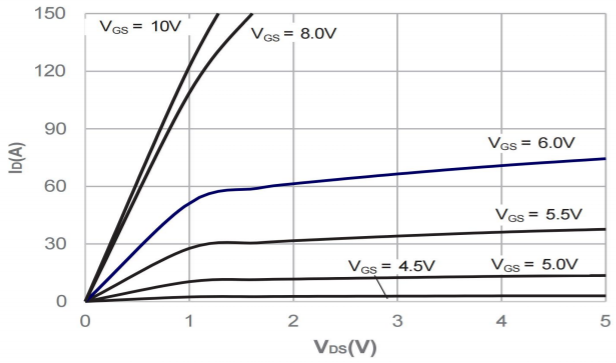


Figure 6: Typical Transfer Characteristics

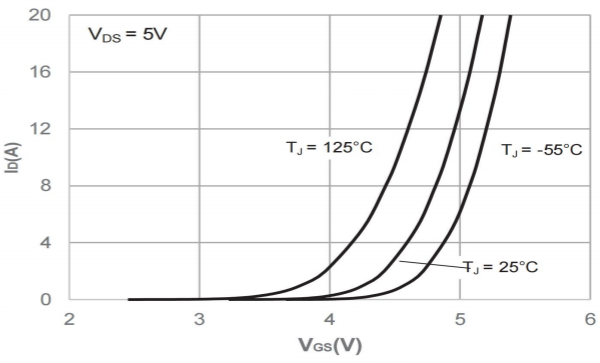


Figure 7: On-resistance vs. Drain Current

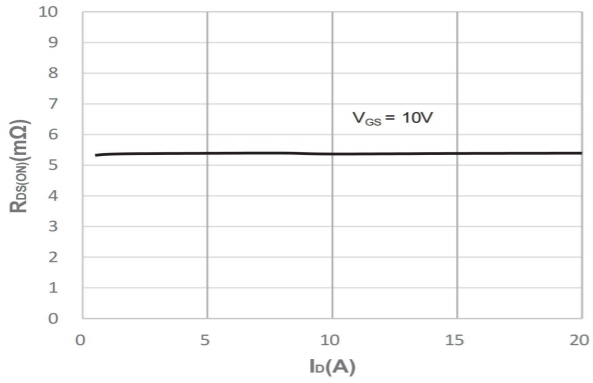


Figure 8: Body Diode Characteristics

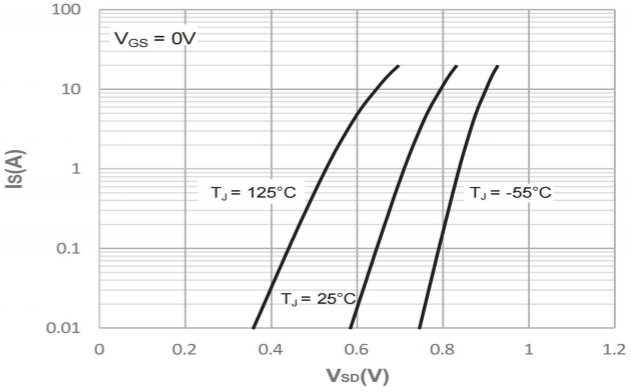


Figure 9: Gate Charge Characteristics

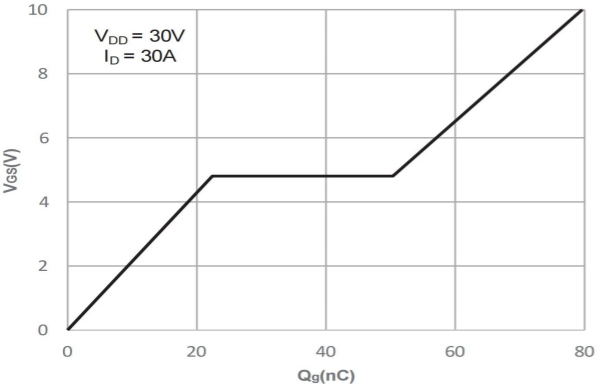
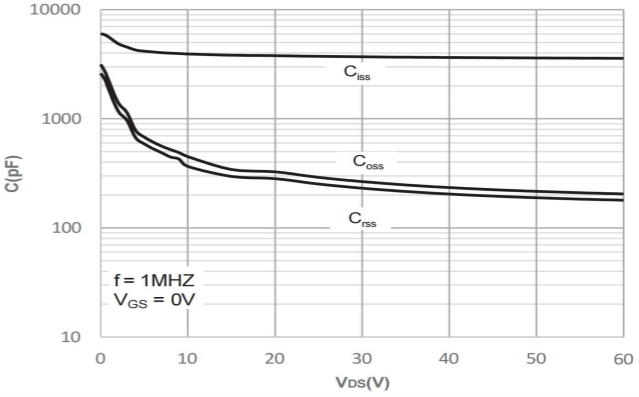


Figure 10: Capacitance Characteristics



Typical Performance Characteristics

Figure 11: Normalized Breakdown voltage vs. Junction Temperature

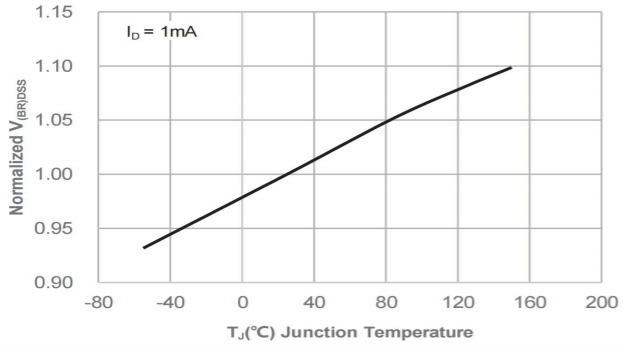


Figure 12: Normalized on Resistance vs. Junction Temperature

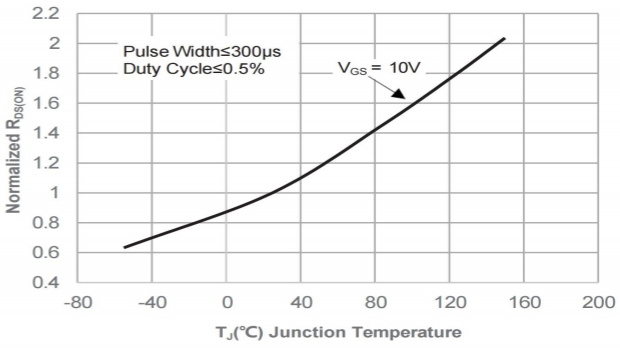


Figure 13: Normalized Threshold Voltage vs. Junction Temperature

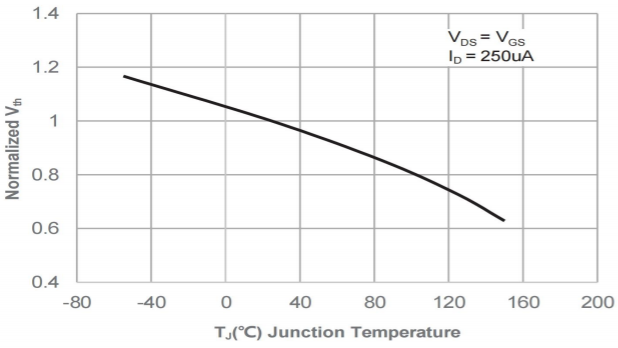


Figure 14: $R_{DS(ON)}$ vs. V_{GS}

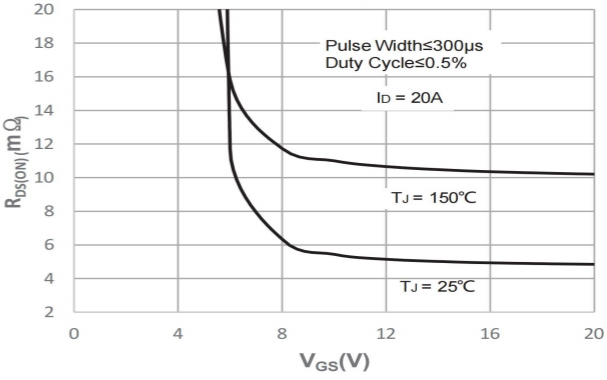
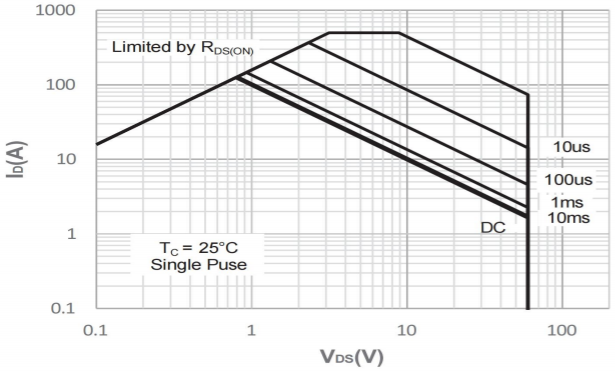


Figure 15: Maximum Safe Operating Area



Test Circuit

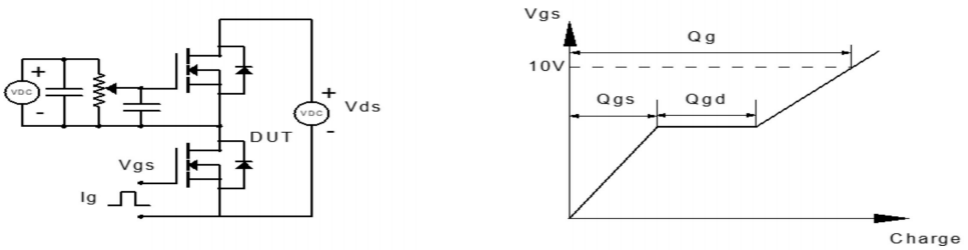


Figure 1: Gate Charge Test Circuit & Waveform

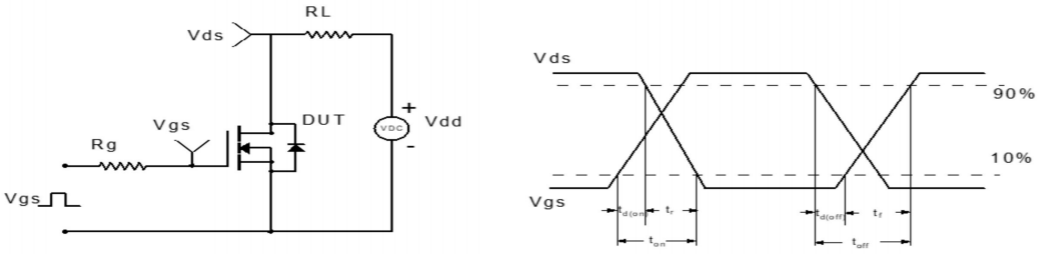


Figure 2: Resistive Switching Test Circuit & Waveform

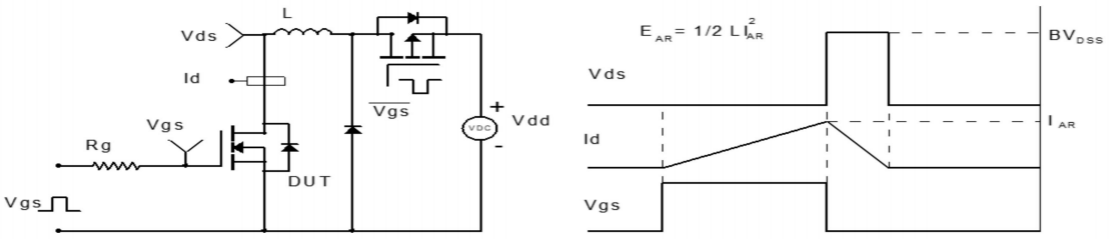


Figure 3: Unclamped Inductive Switching Test Circuit& Waveform

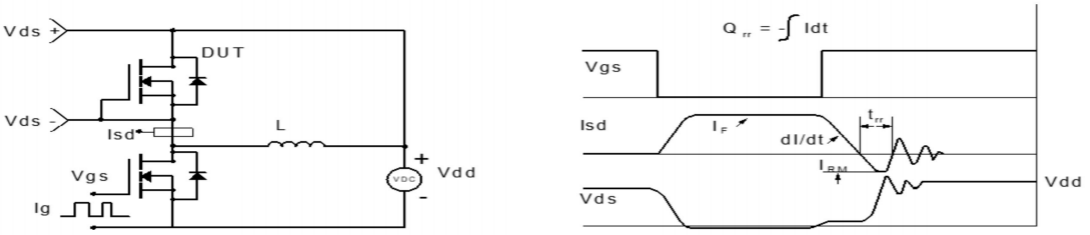


Figure 4: Diode Recovery Test Circuit & Waveform